TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH245FK

Octal Bus Transceiver

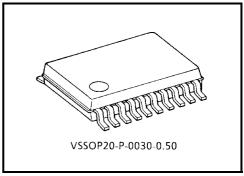
The TC7MH245FK is an advanced high speed CMOS octal bus transceiver fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

It is intended for two-way asynchronous communication between data busses. The direction of data transmission is determined by the level of the DIR input.

The enable input (\overline{G}) can be used to disable the device so that the busses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

- High speed: $t_{pd} = 4.0 \text{ ns (typ.) (V}_{CC} = 5 \text{ V)}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Balanced propagation delays: $t_pLH \approx t_pHL$
- Wide operating voltage range: $VCC (opr) = 2 \sim 5.5 \text{ V}$
- Low noise: VOLP = 1.0 V (max)
- Pin and function compatible with 74ALS245

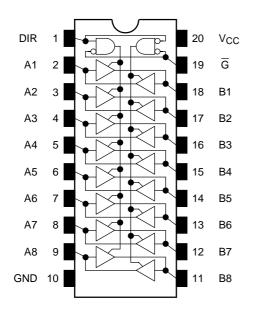
Note: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

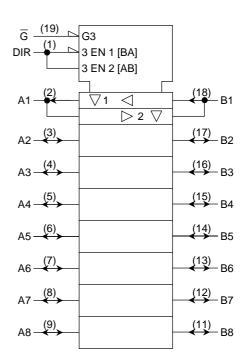
A parasitic diode is formed between the bus and V_{CC} terminals. Therefore bus terminal can not be used to interface 5 V to 3 V systems directly.

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Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inputs		Outputs	Function			
G	DIR			B-Bus		
L	L	A = B	Output	Input		
L	Н	B = A	Input	Output		
Н	Х	Z	Z			

X: Don't care

Z: High impedance

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage (DIR, \overline{G})	V _{IN}	-0.5~7.0	V
DC bus I/O voltage	V _{I/O}	-0.5~V _{CC} + 0.5	V
Input diode current (DIR, \overline{G})	lıĸ	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	I _{OUT}	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

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Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	2.0~5.5	V	
Input voltage (DIR, \overline{G})	V _{IN}	0~5.5	V	
Bus I/O voltage	V _{I/O}	0~V _{CC}	V	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V	
input noe and rail time	αί/αν	$0 \sim 20 \ (V_{CC} = 5 \pm 0.5 \ V)$	113/ V	

Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test C		Condition		Ta = 25°C			Ta = -40~85°C		Unit
		Symbol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
land to the sec			-		2.0	1.50	_	_	1.50	_	V
	High level	V _{IH}			3.0~5.5	V _{CC} × 0.7	_	_	V _{CC} × 0.7	_	
Input voltage			_		2.0		_	0.50	_	0.50	V
	Low level	V _{IL}			3.0~5.5		_	V _{CC} × 0.3	_	V _{CC} × 0.3	
				Ι _{ΟΗ} = –50 μΑ	2.0	1.9	2.0	_	1.9	_	V
	High level	Vон	V _{IN} = V _{IH} or V _{IL}		3.0	2.9	3.0	_	2.9	_	
					4.5	4.4	4.5	_	4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
Output				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
voltage	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	Ι _{ΟL} = 50 μΑ	2.0		0	0.1	_	0.1	
					3.0		0	0.1	_	0.1	
					4.5		0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0		_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44	
3-state output off-state current		l _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	_	±0.25	_	±2.50	μА
Input leakage	Input leakage current I _{IN} V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ		
Quiescent supply current		Icc	$V_{IN} = V_{CC}$ or GND		5.5	_		4.0	_	40.0	μΑ

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AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Unit
			3.3 ± 0.3 -	15	_	5.8	8.4	1.0	10.0	ns
Propagation delay time	t _{pLH}			50		8.3	11.9	1.0	13.5	
Tropagation delay time	t _{pHL}	_	5.0 ± 0.5	15		4.0	5.5	1.0	6.5	
			3.0 ± 0.3	50	_	5.5	7.5	1.0	8.5	
		R _L = 1 kΩ	3.3 ± 0.3	15	_	8.5	13.2	1.0	15.5	- ns
3-state output enable time	^t pZL ^t pZH			50	_	11.0	16.7	1.0	19.0	
3-state output enable time			5.0 ± 0.5	15	_	5.8	8.5	1.0	10.0	
				50	_	7.3	10.6	1.0	12.0	
2 state output dipoble time	t _{pLZ}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	50	_	11.5	15.8	1.0	18.0	ns
3-state output disable time	t _{pHZ}		5.0 ± 0.5	50	_	7.0	9.7	1.0	11.0	115
Output to output alcour	t _{osLH} t _{osHL}	(1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	
Output to output skew		(Note1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
Input capacitance	C _{IN}	DIR, G		_	4	10	_	10	pF	
Bus input capacitance	C _{I/O}	A _n , B _n			_	8	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note2)		21		_	_	pF

Note1: This parameter is guaranteed by design.

 $t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|$

Note2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

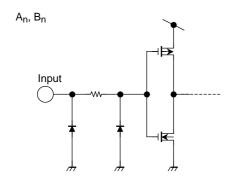
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$

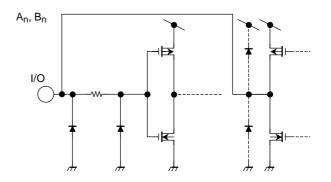
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.7	1.0	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.7	-1.0	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V_{ILD}	C _L = 50 pF	5.0	_	1.5	V

Input Equivalent Circuit

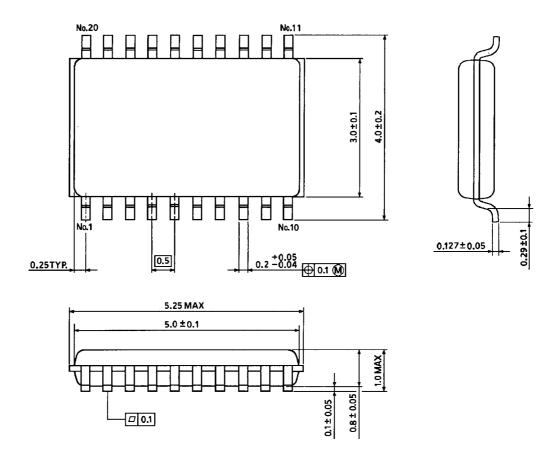
Bus Terminal Equivalent Circuit





Package Dimensions

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Weight: 0.03 g (typ.)

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